

# **isc Silicon NPN Darlington Power Transistor**

### **DESCRIPTION**

- · High DC Current Gain
  - : h<sub>FE</sub>= 1500(Min.)@ I<sub>C</sub>= 4A, V<sub>CE</sub>= 3V
- · Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO} = 100V(Min.)$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

# **APPLICATIONS**

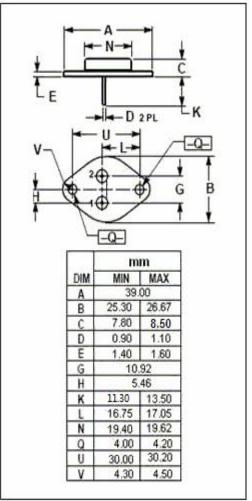


• Designed for motor drivers, printer hammer drivers, relay drivers, voltage regulator control applications.

# N 1.Base 2.Emitter 3.Collestor(case) TO-3 Package

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	110	V
V <sub>CEO</sub>	Collector-Emitter Voltage	100	٧
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current-Continuous	8	А
Ісм	Collector Current-Peak	12	А
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	70	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$





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2SD1233

## **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C$ = 30mA; $R_{BE}$ = $\infty$	100			V		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	110			V		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A, I <sub>B</sub> = 8mA			1.5	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A, I <sub>B</sub> = 8mA			2.0	V		
Ісво	Collector Cutoff current	V <sub>CB</sub> = 80V, I <sub>E</sub> = 0			0.1	mA		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V		20		MHz		
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 3V	1500					
Switching Times								
t <sub>on</sub>	Turn-On Time			0.6		μS		
t <sub>stg</sub>	Storage Time	$I_C = 4A$ , $I_{B1} = I_{B2} = 8mA$ ; $R_L = 12.5 \Omega$ ; $V_{CC} = 50V$		4.8		μS		
t <sub>f</sub>	Fall Time			1.6		μS		

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